NST857BF3T5G

PNP General Purpose Transistor

The NST857BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 220-475
- Low $V_{CE(sat)}$, $\leq -0.3 \text{ V}$
- Reduces Board Space
- This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-45	Vdc
Collector - Base Voltage	V _{CBO}	-50	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	432	°C/W
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R _{ΨJL} (Note 2)	143	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

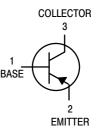
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 100 mm² 1 oz, copper traces.
- 2. 500 mm² 1 oz, copper traces.



ON Semiconductor®

http://onsemi.com



NST857BF3T5G



SOT-1123 CASE 524AA STYLE 1

MARKING DIAGRAM



5 = Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST857BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST857BF3T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I _C = -10 mA)	V _{(BR)CEO}	-45	-	-	٧
Collector - Emitter Breakdown Voltage (I _C = -10 μA, V _{EB} = 0)	V _{(BR)CES}	-50	-	-	٧
Collector – Base Breakdown Voltage (I _C = -10 μA)	V _{(BR)CBO}	-50	-	-	٧
Emitter – Base Breakdown Voltage (I _E = –1.0 μA)	V _{(BR)EBO}	-5.0	-	-	٧
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150 ^{\circ}\text{C}$)	I _{CBO}	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain	h _{FE}	- 220	150 290	- 475	_
Collector – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{CE(sat)}	- -	- -	-0.3 -0.7	V
Base – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{BE(sat)}	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage (I_C = -2.0 mA, V_{CE} = -5.0 V) (I_C = -10 mA, V_{CE} = -5.0 V)	V _{BE(on)}	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 Vdc, f = 100 MHz)	f _T	100	-	-	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)	C _{obo}	-	-	4.5	pF
Input Capacitance (V _{EB} = -0.5 V, I _C = 0 mA, f = 1.0 MHz)	C _{ibo}	-	-	10	pF
Noise Figure (I _C = -0.2 mA, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	_	-	10	dB

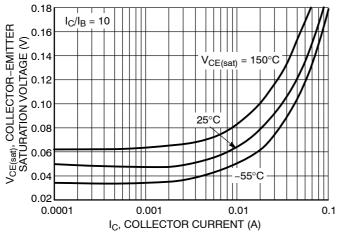


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

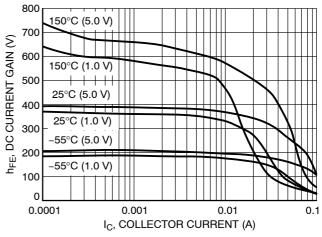


Figure 2. DC Current Gain vs. Collector Current

NST857BF3T5G

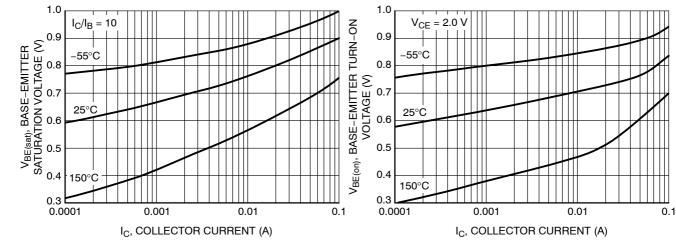


Figure 3. Base Emitter Saturation Voltage vs. **Collector Current**

Figure 4. Base Emitter Turn-On Voltage vs. **Collector Current**

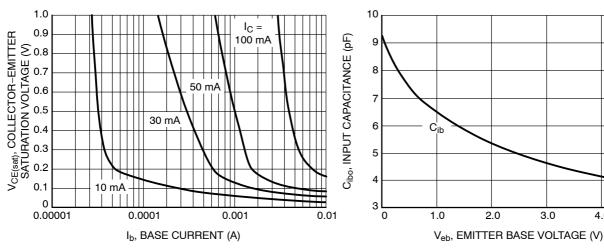


Figure 5. Saturation Region

Figure 6. Input Capacitance

4.0

5.0

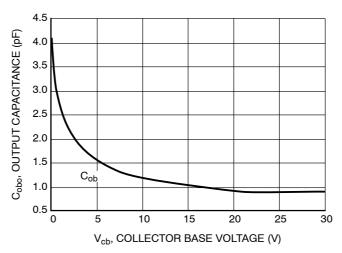


Figure 7. Output Capacitance

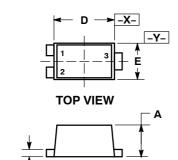




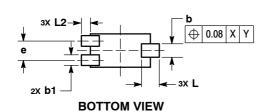
SOT-1123 CASE 524AA **ISSUE C**

DATE 29 NOV 2011

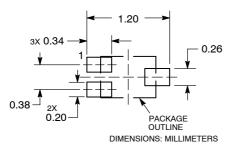
SCALE 8:1



HE SIDE VIEW



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME
- DIMENSIONING AND TOLERANOR PER ASM Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.34	0.40		
b	0.15	0.28		
b1	0.10	0.20		
С	0.07	0.17		
D	0.75	0.85		
Ε	0.55	0.65		
е	0.35	0.40		
HE	0.95	1.05		
L	0.185 REF			
L2	0.05	0.15		

GENERIC MARKING DIAGRAM*



= Specific Device Code

= Date Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	CATHODE	2. SOURCE
3. COLLECTOR	CATHODE	CATHODE	ANODE	3. DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA

2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E UMX21NTR EMT2T2R MCH6102-TL-E FP204-TL-E

NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13

NTE15 NTE16001